

# Lecture 18

## Transistor Amplifiers (I)

### Common-Source Amplifier

#### Outline

- Amplifier fundamentals
- Common-source amplifier
- Common-source amplifier with current-source supply

#### **Reading Assignment:**

Howe and Sodini; Chapter 8, Sections 8.1-8.4

#### **Announcement:**

**Quiz #2:** November 15, 7:30-9:30 PM at Walker.

Calculator Required. Open book.

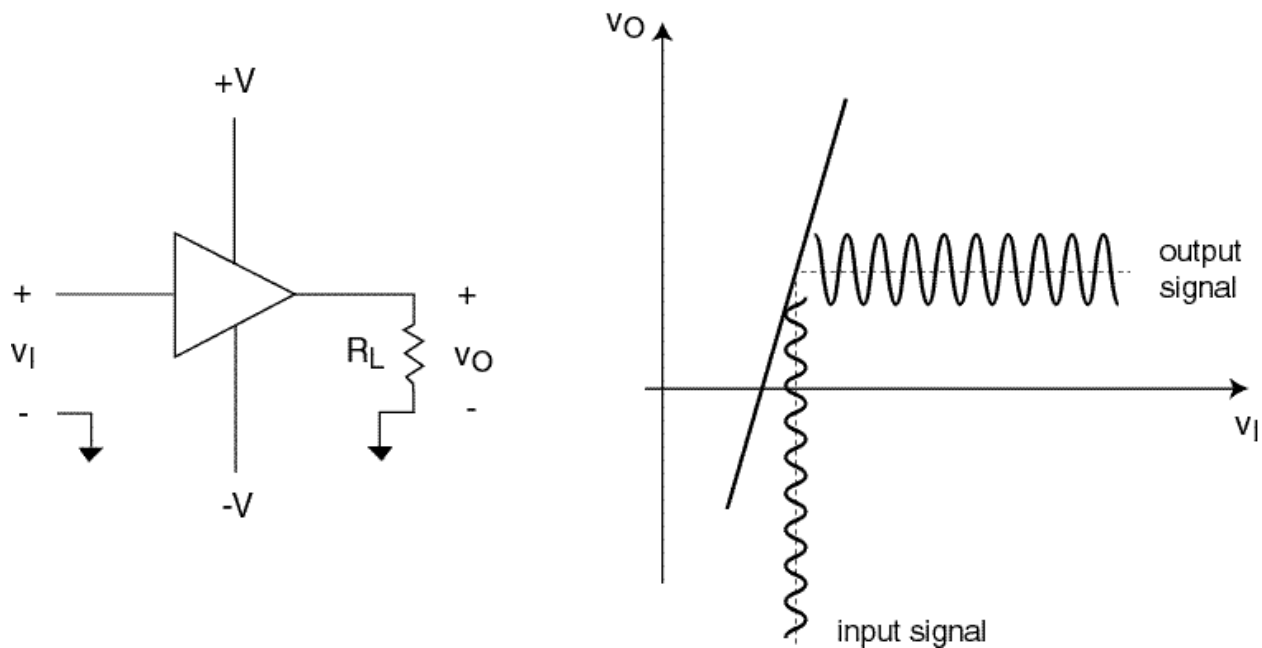
**Quiz Review:** Monday, Nov. 13, 7:30-9:30, Rm. 1-390

# Summary of Key Concepts

- Figures of merit of an amplifier
  - Gain
  - Signal swing
  - Power consumption
  - Frequency response
  - Immunity to process and temperature variations
- Common-source amplifier with resistive supply
  - For high gain, large  $R_D$  required
  - Large  $R_D$  consumes a lot of Si real estate.
  - Large  $R_D$  eventually compromises frequency response
- Performance of common-source amplifier improved using current source supply.
- Computation of two-port network parameters of a voltage amplifier
  - voltage gain, input resistance and output resistance

# 1. Amplifier fundamentals

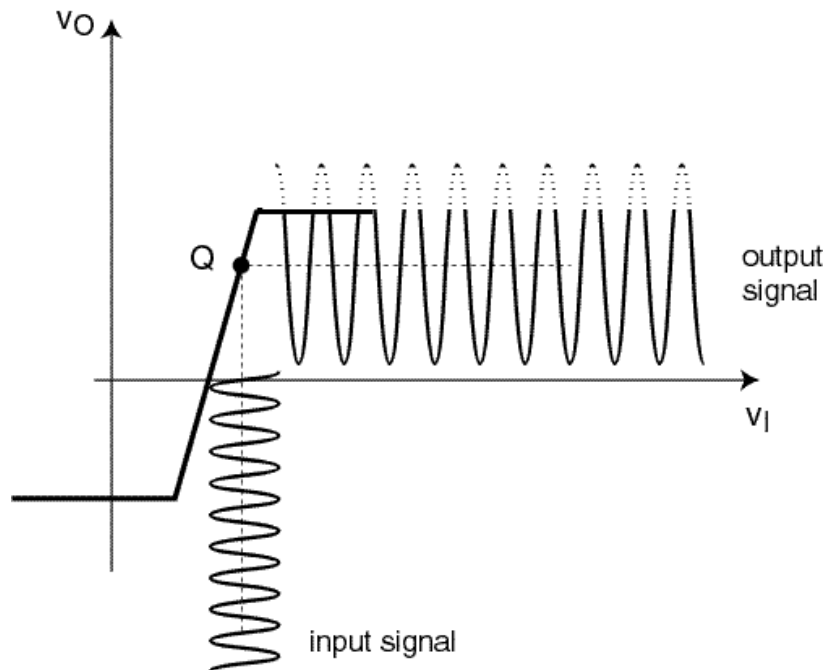
Goal of amplifiers: *signal amplification*



Features of amplifier:

- ***Output signal*** is faithful replica of ***input signal*** but amplified in magnitude.
- Amplifier exhibits ***power gain***:
  - Control of the flow of energy from power supply to output load in response to input signal.
- ***Active device*** is at the heart of amplifier
- Need ***linear transfer characteristics*** for distortion not to be introduced.

## “More Realistic” Transfer Characteristics



- Transfer characteristics linear over limited range of voltages: **amplifier saturation**
- Amplifier saturation limits signal swing.
- Signal swing also depends on choice of **bias point**,  $Q$  (also called **quiescent point** or **operating point**).

Other features desired in amplifiers:

- Low **power consumption**.
- Wide **frequency response** [will discuss in a few days].
- Immunity to process and temperature variations.

## 2. Common-Source Amplifier:

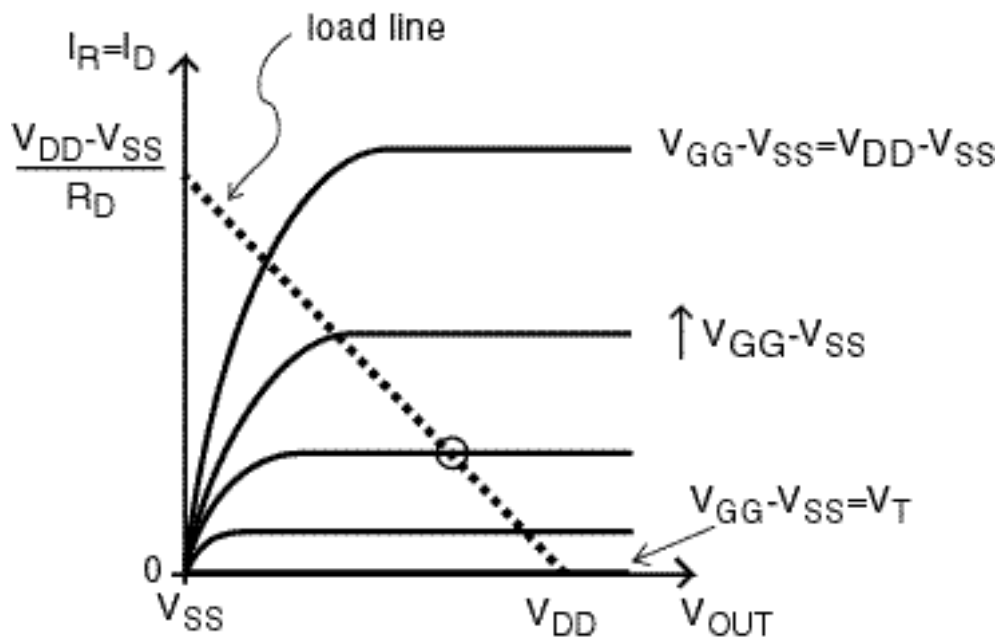
Consider the following circuit:

Consider it first unloaded by  $R_L$ . How does it work?

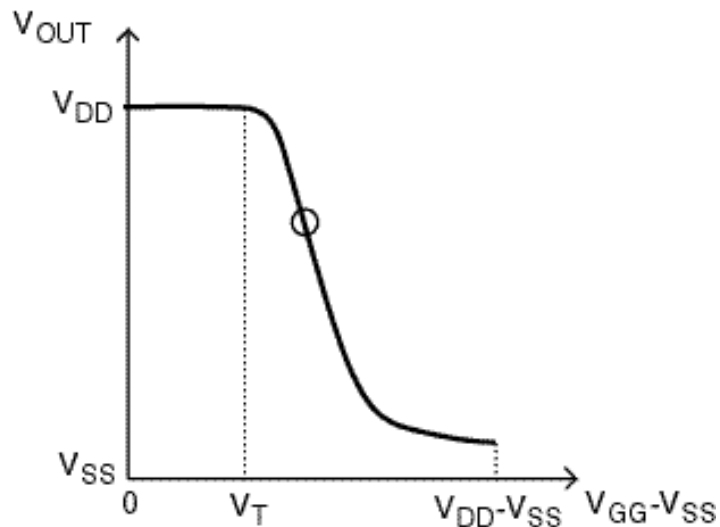
- $V_{GG}$ ,  $R_D$  and  $W/L$  of MOSFET selected to bias transistor in saturation and obtain desired output bias point (i.e.  $V_{OUT} = 0$ ).
- $v_{GS}$        $i_D$        $i_R$        $v_{OUT}$
- $A_v = v_{out} / v_s < 0$ ; output out of phase from input, but if amplifier is well designed,  $|A_v| > 1$ .

Watch notation:  $v_{OUT}(t) = V_{OUT} + v_{out}(t)$

## Load line view of amplifier:



## Transfer characteristics of amplifier:



Want:

- Bias point calculation;
- Small-signal gain;
- Limits to signal swing
- Frequency response [in a few days]

**Bias point:** choice of  $V_{GG}$ ,  $W/L$ , and  $R_D$  to keep transistor in saturation and to get proper quiescent  $V_{OUT}$ .

Assume MOSFET is in saturation:

$$I_D = \frac{W}{2L} \mu_n C_{ox} (V_{GG} - V_{SS} - V_T)^2$$

$$I_R = \frac{V_{DD} - V_{OUT}}{R_D}$$

If we select  $V_{OUT}=0$ :

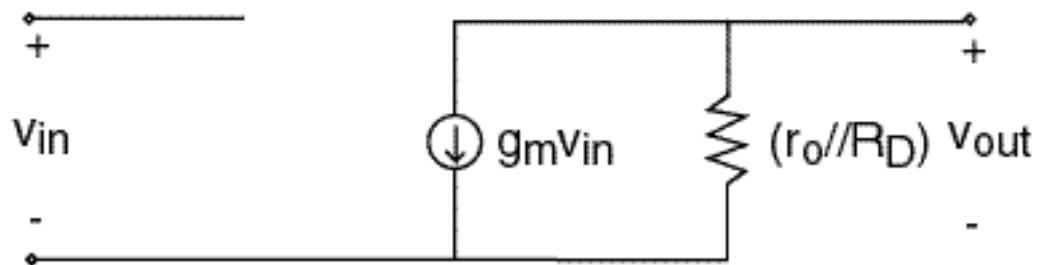
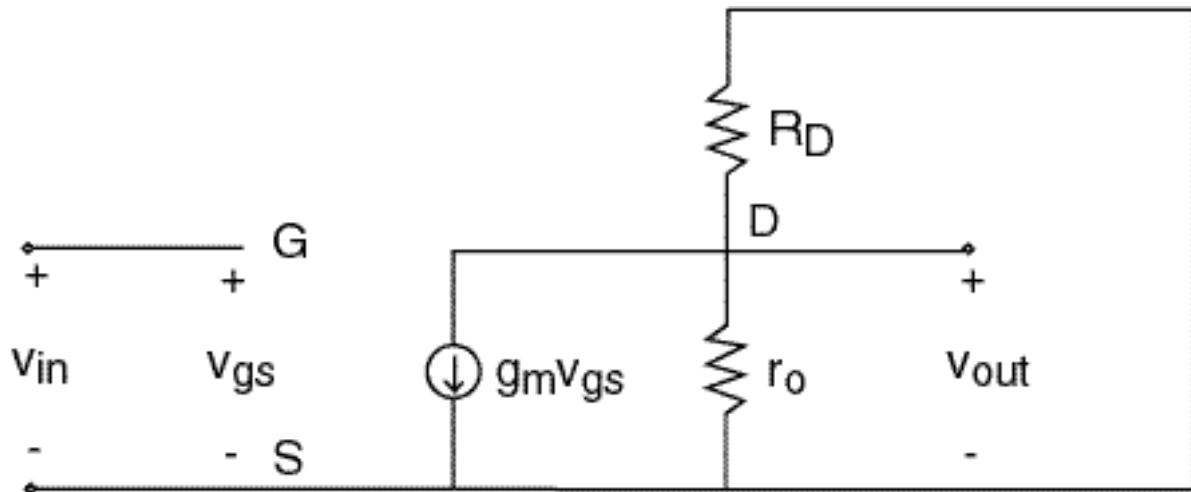
$$I_D = I_R = \frac{W}{2L} \mu_n C_{ox} (V_{GG} - V_{SS} - V_T)^2 = \frac{V_{DD}}{R_D}$$

Then:

$$V_{GG} = \sqrt{\frac{2 V_{DD}}{R_D \frac{W}{L} \mu_n C_{ox}}} - V_{SS} - V_T$$

Equation that allows us to compute needed  $V_{GG}$  given  $R_D$  and  $W/L$ .

**Small-signal voltage gain:** draw small-signal equivalent circuit model:

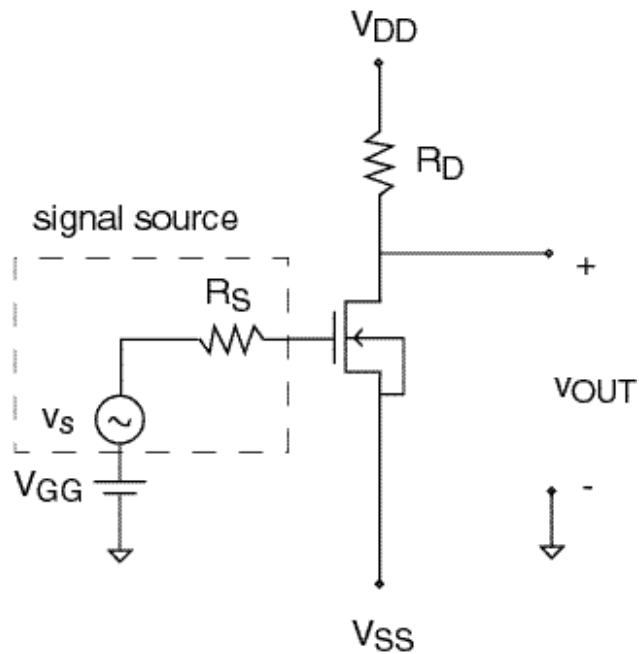


$$v_{out} = -g_m v_{in} (r_o // R_D)$$

Then unloaded voltage gain:

$$A_{vO} = \frac{v_{out}}{v_{in}} = -g_m (r_o // R_D)$$

## Signal swing:



- Upswing: limited by MOSFET going into cut-off.

$$V_{out,max} = V_{DD}$$

- Downswing: limited by MOSFET leaving saturation.

$$V_{DS,sat} = V_{GS} - V_T$$

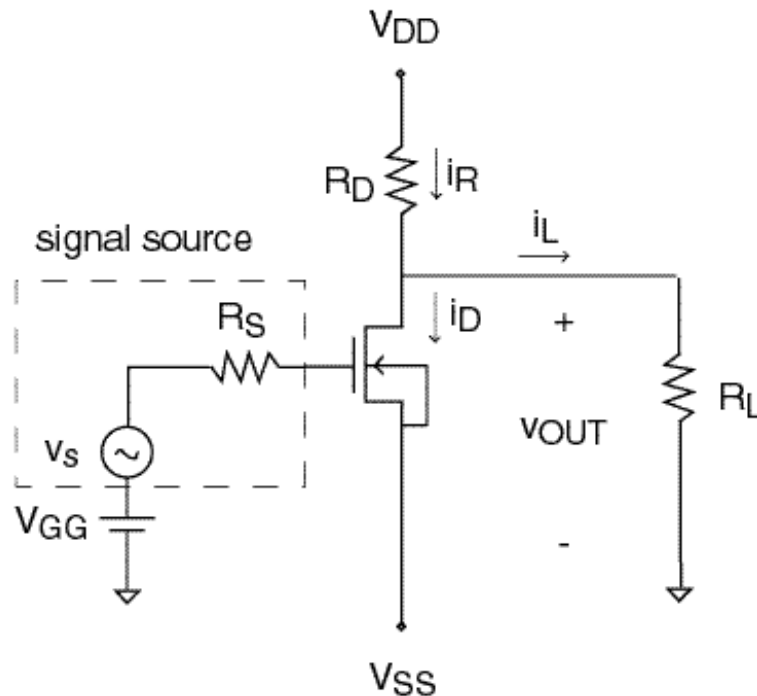
or

$$V_{out,min} - V_{SS} = V_{GG} - V_{SS} - V_T$$

Then:

$$V_{out,min} = V_{GG} - V_T$$

## Effect of input/output loading:



- Bias point not affected because selected  $V_{OUT}=0$ .
- Upswing limited by resistive divider:

$$v_{out,max} = V_{DD} \frac{R_L}{R_L + R_D}$$

- Downswing not affected by loading
- Voltage gain:
  - Input loading ( $R_s$ ): no effect because the gate does not draw any current;
  - Output loading ( $R_L$ ):  $R_L$  reduces voltage gain because it draws current.

$$|A_v| = g_m (r_o // R_D // R_L) < g_m (r_o // R_D)$$

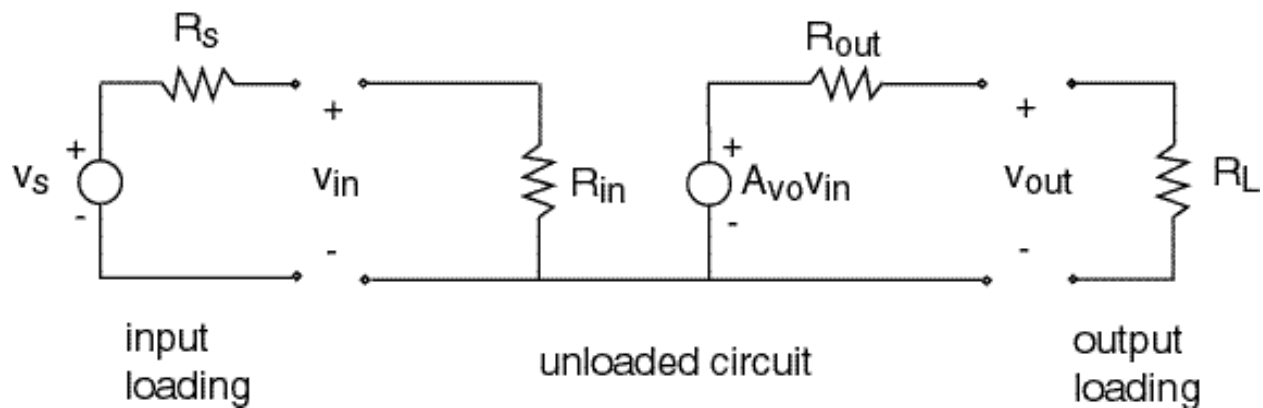
## Generic view of the effect of loading on small-signal operation

Two-port network view of small-signal equivalent circuit model of a voltage amplifier:

$R_{in}$  is *input resistance*

$R_{out}$  is *output resistance*

$A_{vo}$  is *unloaded voltage gain*



Voltage divider at input: 
$$v_{in} = R_{in} \frac{v_s}{R_{in} + R_s}$$

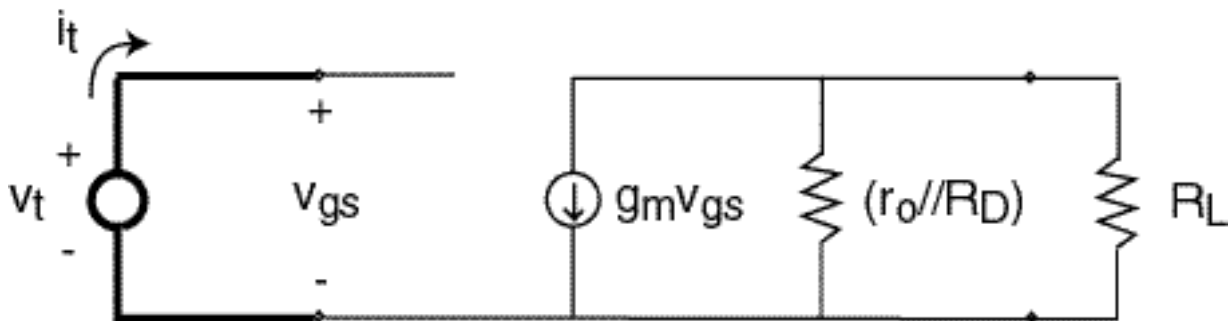
Voltage divider at output: 
$$v_{out} = R_L \frac{A_{vo} v_{in}}{R_{out} + R_L}$$

Loaded voltage gain: 
$$\frac{v_{out}}{v_s} = \frac{R_{in}}{R_{in} + R_s} A_{vo} \frac{R_L}{R_L + R_{out}}$$

# Input Resistance

- Calculation of input resistance,  $R_{in}$ :
  - Load amplifier with  $R_L$
  - Apply test voltage (or current) at input, measure test current (or voltage).

For common-source amplifier:



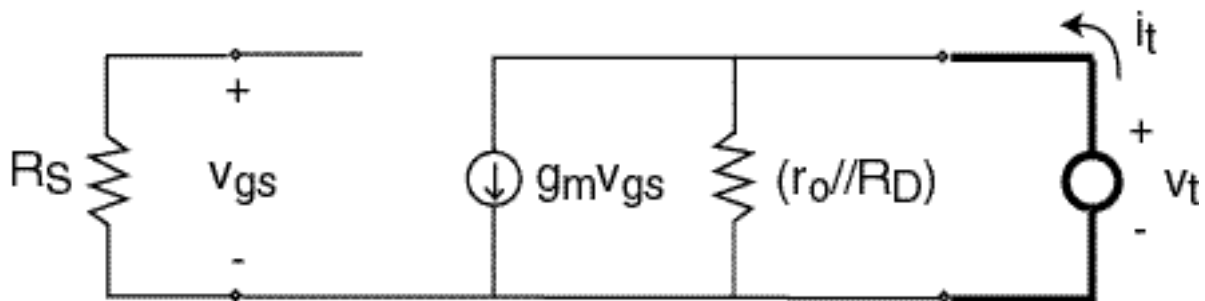
$$i_t = 0 \quad R_{in} = \frac{v_t}{i_t} =$$

No effect of loading at input.

# Output Resistance

- Calculation of output resistance,  $R_{out}$ :
  - Load amplifier with  $R_S$
  - Apply test voltage (or current) at output, measure test current (or voltage).

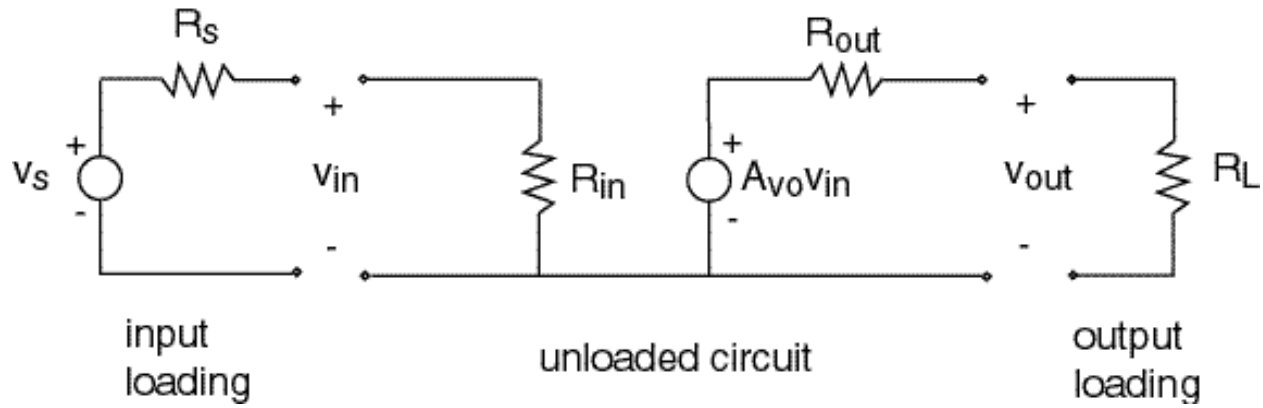
For common-source amplifier:



$$v_{gs} = 0 \quad g_m v_{gs} = 0 \quad v_t = i_t (r_o // R_D)$$

$$R_{out} = \frac{v_t}{i_t} = r_o // R_D$$

## Two-port network view of common-source amplifier



$$\frac{v_{out}}{v_s} = \frac{R_{in}}{R_{in} + R_s} A_{vo} \frac{R_L}{R_L + R_{out}} = -g_m (r_o // R_D) \frac{R_L}{R_L + r_o // R_D}$$

Or:

$$\frac{v_{out}}{v_s} = -g_m (r_o // R_D // R_L)$$

## Design issues of common-source amplifier (unloaded)

- To maximize gain: want  $R_D$  high

$$|A_{vo}| = g_m (r_o \parallel R_D)$$

- To get high  $|A_{vo}|$        $R_D$        $I_D = \frac{V_{DD}}{R_D}$

Rewrite  $|A_{vo}|$  in the following way:

$$|A_{vo}| \quad g_m R_D = \sqrt{2I_D \frac{W}{L} \mu_n C_{ox}} \cdot \frac{V_{DD}}{I_D} \quad \frac{1}{\sqrt{I_D}}$$

Then:

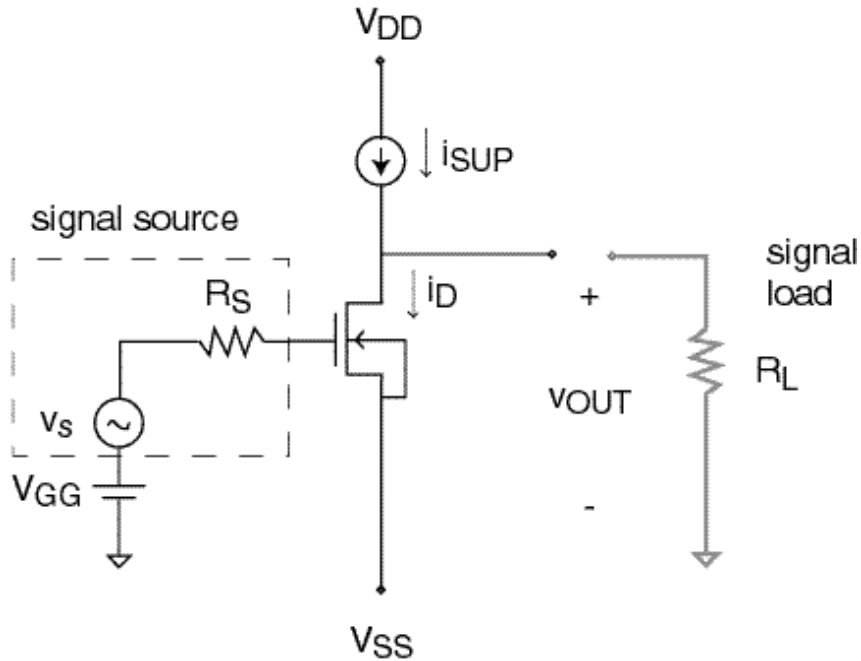
$$R_D \quad I_D \quad g_m \quad |A_{vo}|$$

### Issues:

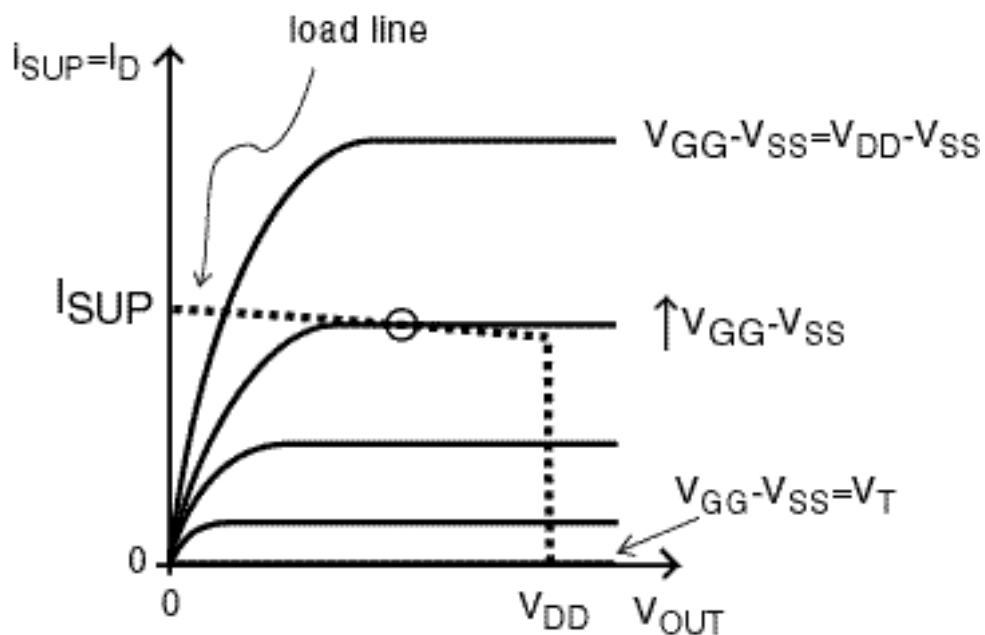
- Large  $R_D$  consumes a lot of Si real estate.
- Large  $R_D$  eventually compromises frequency response

**Solution:** CS amplifier with current source supply

### 3. Common-source amplifier with current-source supply



Loadline view:



### 3. Common-source amplifier with current-source supply (contd.)

Current source characterized by high output resistance:

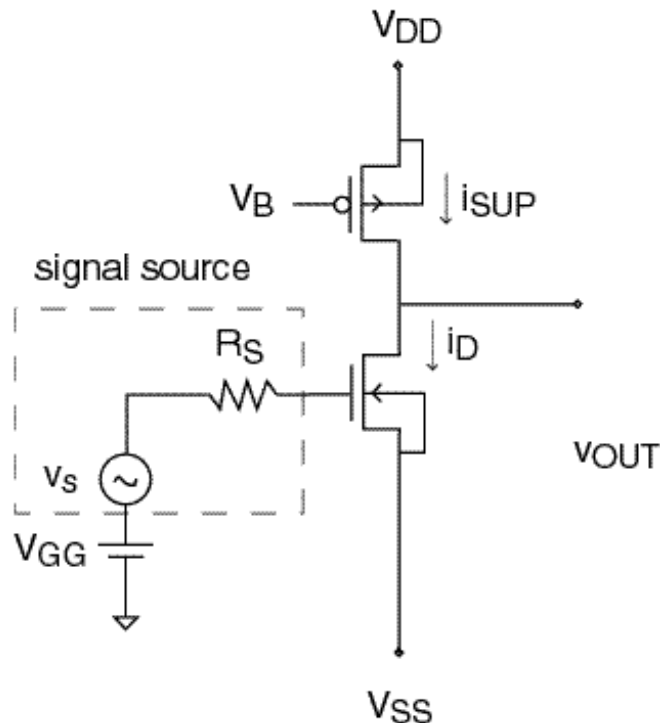
$$r_{\text{out}} = r_{\text{oc}}$$

Voltage gain:

$$|A_{\text{vo}}| = g_m (r_o // r_{\text{oc}})$$

significantly higher than amplifier with resistive supply.

Can implement current source supply by means of p-channel MOSFET:



# What did we learn today?

## Summary of Key Concepts

- Figures of merit of an amplifier
  - Gain
  - Signal swing
  - Power consumption
  - Frequency response
  - Immunity to process and temperature variations
- Common-source amplifier with resistive supply
  - For high gain, large  $R_D$  required
  - Large  $R_D$  consumes a lot of Si real estate.
  - Large  $R_D$  eventually compromises frequency response
- Performance of common-source amplifier improved using current source supply.
- Computation of two-port network parameters of a voltage amplifier
  - voltage gain, input resistance and output resistance